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Januray 2014

FQD11P06 / FQU11P06

P-Channel QFET® MOSFET

-60 V, -9.4 A, 185 mΩ

Description

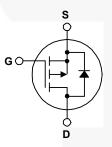
This P-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance • Low Crss (Typ. 45 pF) and high avalanche energy strength. These devices are suitable for switched mode power supplies, audio amplifier, • 100% Avalanche Tested DC motor control, and variable switching power applications...

Features

- -9.4 A, -60 V, $R_{DS(on)}$ = 185 m Ω (Max.) @ V_{GS} = -10 V, $I_D = -4.7 A$
- Low Gate Charge (Typ. 13 nC)







Absolute Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol	Parameter	FQD11P06TM / FQU11P06TU	Unit	
V_{DSS}	Drain-Source Voltage	-60	V	
I _D	Drain Current - Continuous (T _C = 25°C)	-9.4	Α	
	- Continuous (T _C = 100°C)	-5.95	Α	
I _{DM}	Drain Current - Pulsed (Not	-37.6	Α	
V _{GSS}	Gate-Source Voltage	± 30	V	
E _{AS}	Single Pulsed Avalanche Energy (Not	2) 160	mJ	
I _{AR}	Avalanche Current (Note	-9.4	Α	
E _{AR}	Repetitive Avalanche Energy (Not	3.8	mJ	
dv/dt	Peak Diode Recovery dv/dt (Note	-7.0	V/ns	
P _D	Power Dissipation (T _A = 25°C) *	2.5	W	
_	Power Dissipation (T _C = 25°C)	38	W	
- Derate above 25°C		0.3	W/°C	
T _J , T _{STG}	Operating and Storage Temperature Range	-55 to +150	°C	
T _L	Maximum lead temperature for soldering, 1/8" from case for 5 seconds	300	°C	

Thermal Characteristics

Symbol	Parameter	FQD11P06TM / FQU11P06TU	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max. 3.28		
Ъ	Thermal Resistance, Junction to Ambient (Minimum Pad of 2-oz Copper), Max.	110	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (*1 in ² Pad of 2-oz Copper), Max.	50	

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FQD11P06TM	FQD11P06	D-PAK	Tape and Reel	330 mm	16 mm	2500 units
FQU11P06TU	FQU11P06	I-PAK	Tube	N/A	N/A	70 units

Flectrical Characteristics

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Off Cha	aracteristics					
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$	-60			V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	I_D = -250 μA, Referenced to 25°C		-0.07		V/°C
I _{DSS}	Zero Oeto Valtono Busin Organia	V _{DS} = -60 V, V _{GS} = 0 V		-	-1	μΑ
	Zero Gate Voltage Drain Current	V _{DS} = -48 V, T _C = 125°C			-10	μΑ
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = -25 V, V _{DS} = 0 V			-100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	V _{GS} = 25 V, V _{DS} = 0 V			100	nA
On Cha	racteristics					
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250 \mu\text{A}$	-2.0		-4.0	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = -10 V, I _D = -4.7 A		0.15	0.185	Ω
9 _{FS}	Forward Transconductance	V _{DS} = -30 V, I _D = -4.7 A		4.9		S
Dynam	ic Characteristics					
C _{iss}	Input Capacitance	V _{DS} = -25 V, V _{GS} = 0 V,		420	550	pF
C _{oss}	Output Capacitance	f = 1.0 MHz		195	250	pF
C _{rss}	Reverse Transfer Capacitance			45	60	pF
Switch	ing Characteristics					
t _{d(on)}	Turn-On Delay Time	V _{DD} = -30 V, I _D = -5.7 A,		6.5	25	ns
t _r	Turn-On Rise Time	$R_{G} = 25 \Omega$		40	90	ns
t _{d(off)}	Turn-Off Delay Time	NG - 20 32		15	40	ns
t _f	Turn-Off Fall Time	(Note 4)		45	100	ns
Qg	Total Gate Charge	V _{DS} = -48 V, I _D = -11.4 A,		13	17	nC
Q _{gs}	Gate-Source Charge	V _{GS} = -10 V	/	2.0		nC
Q _{gd}	Gate-Drain Charge	(Note 4)		6.3		nC
Drain-S	Source Diode Characteristics ar	nd Maximum Ratings			/	
I _S	Maximum Continuous Drain-Source Diode Forward Current				-9.4	Α
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current			-	-37.6	Α
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S = -9.4 A		-	-4.0	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _S = -11.4 A,		83	//	ns
भा						

- **Notes:** 1. Repetitive rating: pulse-width limited by maximum junction temperature. 2. L = 2.1 mH, I_{AS} = -9.4 A, V_{DD} = -25 V, R_G = 25 Ω , starting T_J = 25°C. 3. I_{SD} ≤ -11.4 A, di/dt ≤ 300 A/ μ s, V_{DD} ≤ BV $_{DSS}$, starting T_J = 25°C. 4. Essentially independent of operating temperature.

Typical Characteristics

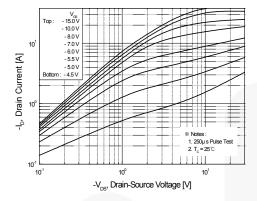


Figure 1. On-Region Characteristics

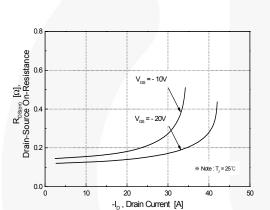


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

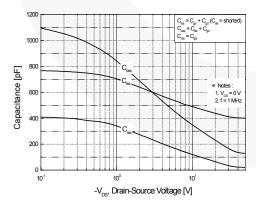


Figure 5. Capacitance Characteristics

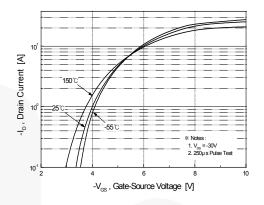


Figure 2. Transfer Characteristics

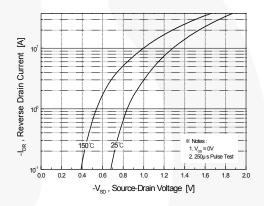


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

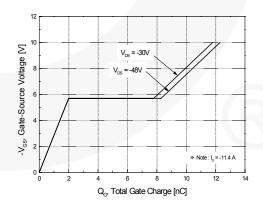


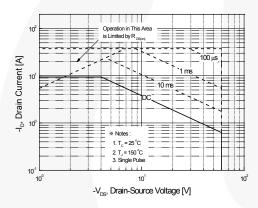
Figure 6. Gate Charge Characteristics

Typical Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

T,, Junction Temperature [°C]

Figure 8. On-Resistance Variation vs. Temperature



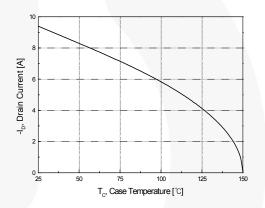


Figure 9. Maximum Safe Operating Area

Figure 10. Maximum Drain Current vs. Case Temperature

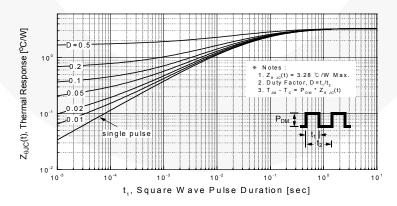


Figure 11. Transient Thermal Response Curve

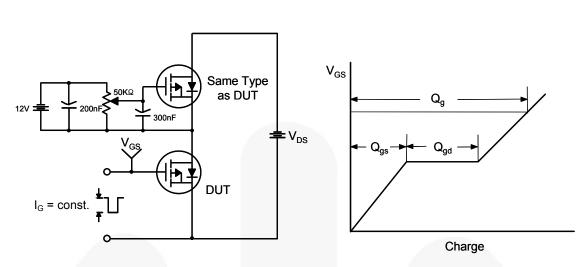


Figure 12. Gate Charge Test Circuit & Waveform

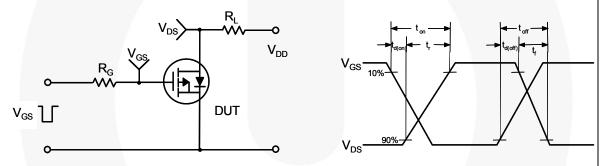


Figure 13. Resistive Switching Test Circuit & Waveforms

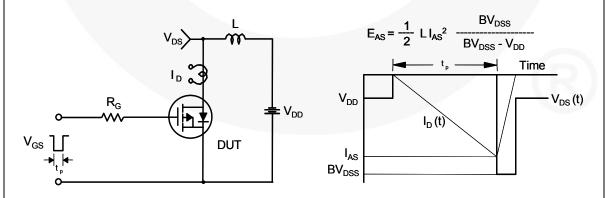
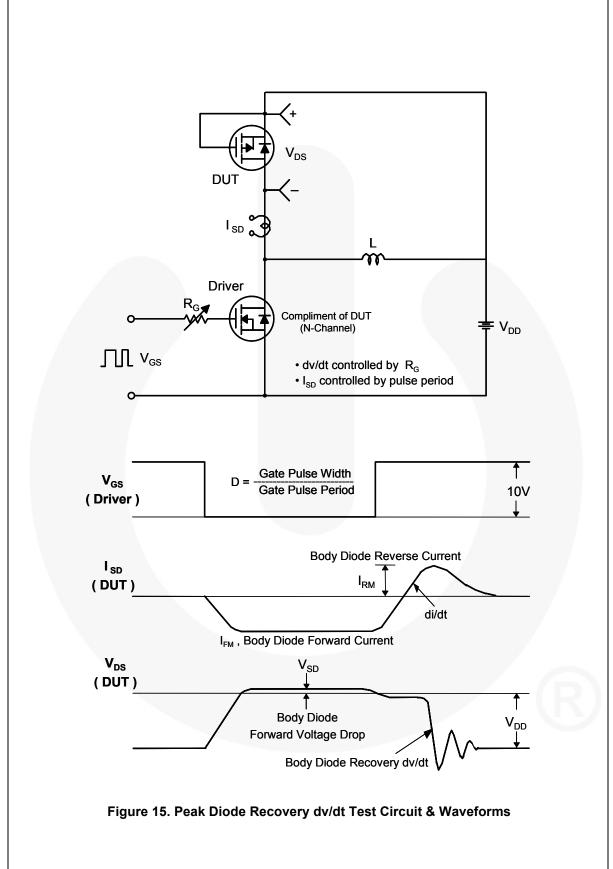


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms



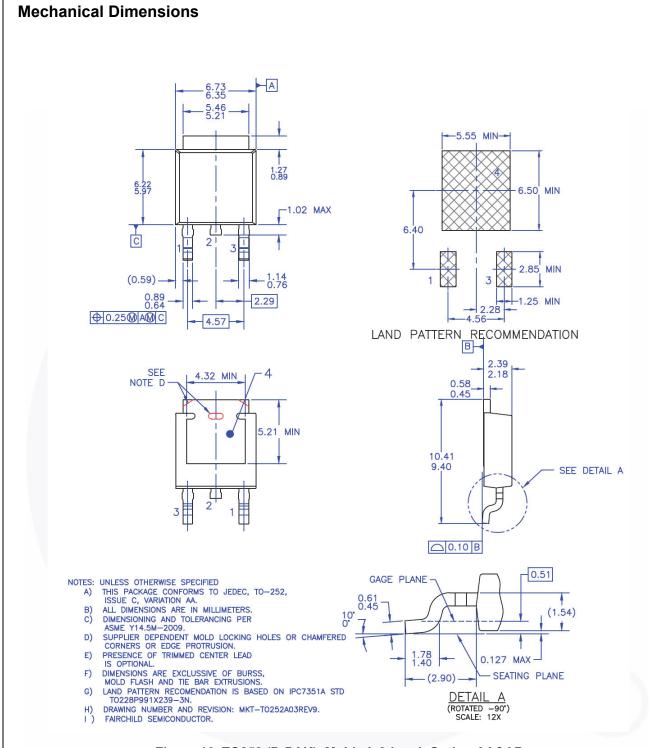


Figure 16. TO252 (D-PAK), Molded, 3-Lead, Option AA&AB

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Mechanical Dimensions C 9.65 8.90 (0.60) -2.29 ◆ 0.25M AM C 3 PLCS NOTES: UNLESS OTHERWISE SPECIFIED ALL DIMENSIONS ARE IN MILLIMETERS.

- B) THIS PACKAGE CONFORMS TO JEDEC, TO-251, ISSUE C, VARIATION AA, DATED SEP 1988.
- C) DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994.

Figure 17. TO251 (I-PAK), Molded, 3-Lead

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